

GOODRAM Industrial M.2 2242 SSD 3D TLC - PB

DATASHEET

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REVISION HISTORY

VERSION	CHANGES	DATE
1.0	Initial release	01.12.2023



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PRODUCT OVERVIEW

Capacity

- · 240, 480, 960GB
- · 256, 512, 1024GB

Form Factor

· M.2 2242-D2-M

PCIe Interface

- PCIe Gen3 x4
- NVMe 1.3
- PCI Express Base 3.1

• Flash Memory

- Transfer rate up to 800MT/s
- $\circ~$ Up to 4pcs of BGA132 flash

Performance^{Note 1}

- Sequential Read: up to 2400 MB/s
- Sequential Write: up to 2000 MB/s

· RoHS compliant

• Power ConsumptionNote 2

- Idle < 30 mW
- ∘ L 1.2 < 5mW

MTBF

o More than 1,500,000 hours

Reliability

○ UBER: <1 sector per 10¹⁶bits

• Advanced Flash Management

- o Static and Dynamic Wear Leveling
- o Bad Block Management
- o TRIM
- o SMART
- o Over-Provision
- o Firmware Update

Power Management

- o Support APST
- o Support ASPM
- o Support L1.2

• Temperature RangeNote 3

- Operational: 0°C +70°C
- Storage: -40°C +85°C

Features Support List:

- o End to end data path protection
- o Thermal throttling
- $\circ SmartZIP^{TM}$
- \circ SmartRefreshTM
- o Drive log
- o Support HMB
- o Support TCG Pyrite

Notes:

- 1. Please refer to "Performance and Power consumption" for details.
- 2. Please refer to "Performance and Power consumption" for details.
- The operation temperature means the case temperature, in which can be decided via the S.M.A.R.T.

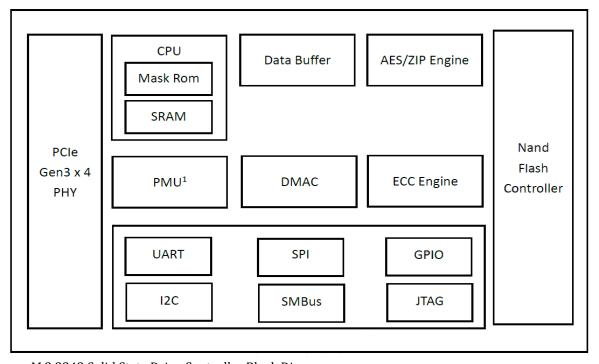


GENERAL DESCRIPTION

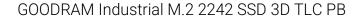
PRODUCT DETAILS

GOODRAM M.2 2242 PB with no external DDR solution delivers all the advantages of flash disc technology with PCIe Gen3 x4 interface and is fully compliant with the standard Next Generation Form Factor (NGFF) called M.2 Card Format. The capacity could provide a wide range up to 1024GB. Meanwhile, the power consumption is much lower than traditional Hard Drives.

CONTROLLER BLOCK DIAGRAM



 $M.2\ 2242\ Solid\ State\ Drive\ Controller\ Block\ Diagram$





FLASH MANAGEMENT

GOODRAM M.2 2242 modules utilize all the state of art technologies to ensure full reliability until the TBW parameter is reached. These technologies include:

Error Correction Code (ECC)

Flash memory cells will deteriorate with use, which might generate random bit errors in the stored data, therefore M.2 2242 applies the LDPC of ECC algorithm, which can detect and correct errors occur during Read process, ensure data been read correctly, as well as protect data from corruption.

Wear Leveling

NAND Flash devices can only undergo a limited number of program/erase cycles, and in most cases, the flash media are not used evenly. If some area get updated more frequently than others, the lifetime of the device would be reduced significantly. Thus, Wear Leveling technique is applied to extend the lifespan of NAND Flash by evenly distributing write and erase cycles across the media. Product has advanced Wear Leveling algorithm, which can efficiently spread out the flash usage through the whole flash media area. Moreover, by implementing both dynamic and static Wear Leveling algorithms, the life expectancy of the NAND Flash is greatly improved.

Bad Block Management

Bad blocks are blocks that include one or more invalid bits, and their reliability is not guaranteed. Blocks that are identified and marked as bad by the manufacturer are referred to as "Early Bad Blocks". Bad blocks that are developed during the lifespan of the flash are named "Later Bad Blocks". We implement an efficient bad block management algorithm to detect the factory-produced bad blocks and manages any bad blocks that appear with use. This practice further prevents data being stored into bad blocks and improves the data reliability.

TRIM

TRIM is a feature which helps improve the read/write performance and speed of solid-state drives (SSD). Unlike hard disk drives (HDD), SSDs are not able to overwrite existing data, so the available space gradually becomes smaller with each use. With the TRIM command, the operating system can inform the SSD which blocks of data are no longer in use and can be removed permanently. Thus, the SSD will perform the erase action, which prevents unused data from occupying blocks all the time.





SMART

SMART, an acronym for Self-Monitoring, Analysis and Reporting Technology, is an open standard that allows a hard disk drive to automatically detect its health and report potential failures. When a failure is recorded by SMART, users can choose to replace the drive to prevent unexpected outage or data loss. Moreover, SMART can inform users of impending failures while there is still time to perform proactive actions, such as copy data to another device.

Over-Provision (Optional)

Over Provisioning refers to the inclusion of extra NAND capacity in a SSD, which is not visible and cannot be used by users. With Over Provisioning, the performance and IOPS (Input/Output Operations per Second) is improved by providing the controller additional space to manage P/E cycles, which enhances the reliability and endurance as well. Moreover, the write amplification of the SSD becomes lower when the controller writes data to the flash.

Firmware Upgrade

Firmware can be considered as a set of instructions on how the device communicates with the host. Firmware will be upgraded when new features are added, compatibility issues are fixed or read/write performance gets improved.

ADDITIONAL FEATURES

Advanced Device Security Features (Secure Erase)

Secure Erase is a standard NVMe command and will write all "0x00" to fully wipe all the data on hard drives and SSDs. When this command is issued, the SSD controller will empty its storage blocks and return to its factory default settings.



PERFORMANCE AND POWER CONSUMPTION

		Performance					
Capacity	Flash Structure (BGA	CrystalDiskMark		IOMeter		ATTO	
	Package)	Read (MB/s)	Write (MB/s)	Read (IOPS)	Write (IOPS)	Read (MB/s)	Write (MB/s)
240GB, 256GB	128GB x 2	2250	1300	85k	280k	3200	3100
480GB, 512GB	256GB x 2	2300	1850	145k	400k	3200	3100
960GB, 1024GB	256GB x 4	2400	2000	200k	420k	3200	3100

NOTES:

- 1. Performance is measured based on the following conditions:
 - (a) CrystalDiskMark 6.0, 1GB range, QD=32T1
 - (b) IOMeter, 1GB range, 4K data size, QD=32T8
 - (c) ATTO, transfer Size 64MB
 - (d) OS Version: Win10 (64bit), version 1809

	Elash Configuration (DCA	Power Consumption3			
Capacity	Flash Configuration (BGA Package)	Read Write PS3 (mW) (mW)		PS3 (mW)	PS4 (mW)
240GB, 256GB	128GB x 2	3000	2785	30	5
480GB, 512GB	256GB x 2	3060	3500	30	5
960GB, 1024GB	256GB x 4	3155	3670	30	5

NOTES:

- 1. Data measured based on YMTC TAS 512Gb mono die TLC Flash.
- 2. Power consumption is measured during the sequential read and write operations performed by IOMeter.



TBW

Capacity	TBW
240/256 GB	>200 TB
480/512 GB	>400 TB
960/1024 GB	>800 TB

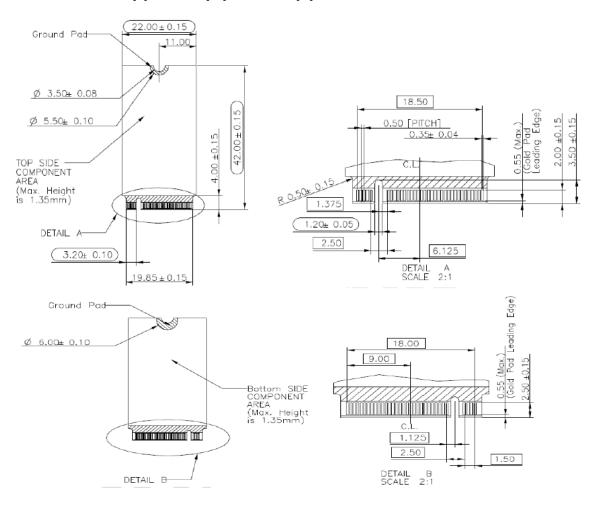
SUPPLY VOLTAGE

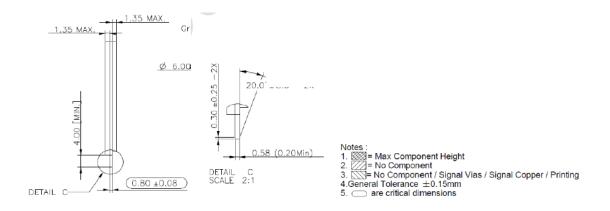
PARAMETER	RATING
Operating voltage	3.3V +/- 5%



PHYSICAL DIMENSION

Dimension: 42mm(L) x 22mm(W) x 2.15mm(H)







PIN ASSIGNMENT AND DESCRIPTIONS

Pin No.	PCIe Pin	Description
1	GND	CONFIG_3 = GND
2	3.3V	3.3V source
3	GND	Ground
4	3.3V	3.3V source
5	PETn3	PCIe TX Differential signal defined by the PCI Express M.2 spec
6	N/C	No connect
7	РЕТр3	PCIe TX Differential signal defined by the PCI Express M.2 spec
8	N/C	No connect
9	GND	Ground
10	LED1#	Open drain, active low signal. These signals are used to allow the add-in card to provide status indicators via LED devices that will be provided by the system.
11	PERn3	PCIe RX Differential signal defined by the PCI Express M.2 spec
12	3.3V	3.3V source
13	PERp3	PCIe RX Differential signal defined by the PCI Express M.2 spec
14	3.3V	3.3V source
15	GND	Ground
16	3.3V	3.3V source
17	PETn2	PCIe TX Differential signal defined by the PCI Express M.2 spec
18	3.3V	3.3V source
19	PETp2	PCIe TX Differential signal defined by the PCI Express M.2 spec
20	N/C	No connect
21	GND	Ground
22	N/C	No connect
23	PERn2	PCIe RX Differential signal defined by the PCI Express M.2 spec
24	N/C	No connect
25	PERp2	PCIe RX Differential signal defined by the PCI Express M.2 spec
26	N/C	No connect
27	GND	Ground
28	N/C	No connect
29	PETn1	PCIe TX Differential signal defined by the PCI Express M.2 spec
30	N/C	No connect
31	PETp1	PCIe TX Differential signal defined by the PCI Express M.2 spec
32	GND	No connect
33	GND	Ground



34	N/C	No connect
35	PERn1	PCIe RX Differential signal defined by the PCI Express M.2 spec
36	N/C	No connect
37	PERp1	PCIe RX Differential signal defined by the PCI Express M.2 spec

Pin No.	PCIe Pin	Description
38	GND	Ground
39	GND	Ground
40	SMB_CLK (I/O)(0/1.8V)	SMBus Clock; Open Drain with pull-up on platform
41	PETn0	PCIe TX Differential signal defined by the PCI Express M.2 spec
42	SMB_DATA (I/O)(0/1.8V)	SMBus Data; Open Drain with pull-up on platform.
43	PETp0	PCIe TX Differential signal defined by the PCI Express M.2 spec
44	ALERT#(0) (0/1.8V)	Alert notification to master; Open Drain with pull-up on platform; Active low.
45	GND	Ground
46	N/C	No connect
47	PERn0	PCIe RX Differential signal defined by the PCI Express M.2 spec
48	N/C	No connect
49	PERp0	PCIe RX Differential signal defined by the PCI Express M.2 spec
50	PERST#(I)(0/3.3V)	PE-Reset is a functional reset to the card as defined by the PCIe Mini CEM specification.
51	GND	Ground
52	CLKREQ#(I/O)(0/3.3V)	Clock Request is a reference clock request signal as defined by the PCIe Mini CEM specification; Also used by L1 PM Substates.
53	REFCLKn	PCIe Reference Clock signals (100 MHz) defined by the PCI Express M.2 spec.
54	PEWAKE#(I/O)(0/3.3V)	PCIe PME Wake. Open Drain with pull up on platform; Active Low.
55	REFCLKp	PCIe Reference Clock signals (100 MHz) defined by the PCI Express M.2 spec.
56	Reserved for MFG DATA	Manufacturing Data line. Used for SSD manufacturing only. Not used in normal operation. Pins should be left N/C in platform Socket.
57	GND	Ground
58	Reserved for MFG CLOCK	Manufacturing Clock line. Used for SSD manufacturing only. Not used in normal operation. Pins should be left N/C in platform Socket.



59	Module Key M			
60	Module Key M			
61	Module Key M			
62	Module Key M	Module Ver		
63	Module Key M	Module Key		
64	Module Key M			
65	Module Key M			
66	Module Key M			
67	N/C	No connect		
68	SUSCLK(32KHz) (I)(0/3.3V)	32.768 kHz clock supply input that is provided by the platform chipset to reduce power and cost for the module.		
69	NC	CONFIG_1 = No connect		
70	3.3V	3.3V source		
71	GND	Ground		
72	3.3V	3.3V source		
73	GND	Ground		
74	3.3V	3.3V source		
75	GND	CONFIG_2 = Ground		



NVMe Command List

Admin Commands

Opcode	Command Description
00h	Delete I/O Submission Queue
01h	Create I/O Submission Queue
02h	Get Log Page
04h	Delete I/O Completion Queue
05h	Create I/O Completion Queue
06h	Identify
08h	Abort
09h	Set Features
0Ah	Get Features
0Ch	Asynchronous Event Request
0Dh	Namespace Management
10h	Firmware Activate
11h	Firmware Image Download
14h	Device Self-test
15h	Namespace Attachment
18h	Keep Alive

Admin Commands - NVM Command Set Specific

Opcode	Command Description
80h	Format NVM
81h	Security Send
82h	Security Receive
84h	Sanitize

NVM Commands

Opcode	Command Description
00h	Flush
01h	Write
02h	Read
04h	Write Uncorrectable
05h	Compare
08h	Write Zeroes
09h	Dataset Management



PRODUCT ORDERING INFORMATION

PN	Туре	Capacity	Technology	Temp range
SSD94-2403CG-PB	M.2	240GB	3D TLC	0 — +70°C
SSD94-2563CG-PB	M.2	256GB	3D TLC	0 — +70°C
SSD94-4803CG-PB	M.2	480GB	3D TLC	0 — +70°C
SSD94-5123CG-PB	M.2	512GB	3D TLC	0 — +70°C
SSD94-9603CG-PB	M.2	960GB	3D TLC	0 — +70°C
SSD94-1T03CG-PB	M.2	1024GB	3D TLC	0 — +70°C

STANDARDS & REFERENCES

The following table is to list out the standards that have been adopted for designing the product.

STANDARD USED	ACRONYM/SOURCE		
RoHS	Restriction of Hazardous Substances Directive; please contact us for further information.		
M.2	http://www.pcisig.com		
PCI Express Base 3.0	https://www.pcisig.com/specifications/pciexpress/base3/		
NVM Express Specification Rev.1.3	http://www.nvmexpress.org/		
Solid-State Drive Requirements and Endurance Test Method (JESD219A)	http://www.jedec.org/standards-documents/docs/jesd219a		
CE	Consumer electronics certification; please contact us for further information.		



SAFETY PRECAUTIONS

Do not bend, crush, drop, or place heavy objects on top of the Product. Do not use tweezers, pliers or similar items that could damage the Product. Take particular care when inserting or removing the Product. Stop using the Product when the Product does not work properly. Failure to follow these instructions could result in fire, damage to the Product and/or other property, and/or personal injury including burns and electric shock.

Keep out of reach of small children. Accidental swallowing may cause suffocation or injury. Contact a doctor immediately if you suspect a child has swallowed the Product.

Do not directly touch the interface pins, put them in contact with metal, strike them with hard objects or cause them to short. Do not expose to static electricity.

Do not disassemble or modify the Product. This may cause electric shock, damage to the Product or fire.

NOTES ON USAGE

The Product contains nonvolatile semiconductor memory. Do not use the Product in accordance with a method of usage other than that written in the manual. This may cause the destruction or loss of data.

To protect against accidental data loss, you should back up your data frequently on more than one type of storage media. Wilk Elektronik S.A. assumes no liability for destruction or loss of data recorded on the Card for any reason.

When used over a long period of time or repeatedly, the reading, writing and deleting capabilities of the Product will eventually fail, and the performance speed of the Product may decrease below the original speed specific to the Product's applicable class.

If the Product is to be transferred or destroyed, note that the data it contained may still be recoverable unless it is permanently deleted by third-party deletion software or similar means beforehand.

Product is intended for use in general electronics applications and selected industrial applications and any other specific applications as expressly stated in this document. Product is neither intended nor warranted for use in equipment or systems where failure may cause loss of human life, bodily injury, serious property damage or serious public impact ("Unintended Use"). Unintended Use includes, without limitation, equipment used in nuclear facilities, equipment used in the aerospace industry, medical equipment or equipment used to control combustions or explosions. Do not use Product for Unintended Use unless specifically permitted in this document.

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